



# Dual N-Channel 60-V (D-S), 175°C MOSFET

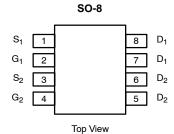
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	
60	0.055 @ V <sub>GS</sub> = 10 V	4.5	
	0.075 @ V <sub>GS</sub> = 4.5 V	3.9	

#### **FEATURES**

- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% R<sub>g</sub> Tested

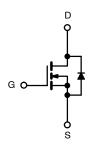


Pb-free Available



Ordering Information: Si4946EY

Si4946EY-T1 (with Tape and Reel)
Si4946EY-E3 (Lead (Pb)-Free)
Si4946EY-E3 (Lead (Pb)-Free with Tape and Reel)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	60	,,		
Gate-Source Voltage		V <sub>GS</sub>	±20			
0 11 0 17 17 17 17 17 17 17 17 17 17 17 17 17	T <sub>A</sub> = 25°C		4.5			
Continuous Drain Current (T <sub>J</sub> = 175°C) <sup>a</sup>	T <sub>A</sub> = 70°C	I <sub>D</sub>	3.8			
Pulsed Drain Current		I <sub>DM</sub>	30	Α		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2			
ngle Avalanche Current		I <sub>AS</sub>	12			
Single Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	7.2	mJ		
	T <sub>A</sub> = 25°C	_	2.4			
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70°C	P <sub>D</sub>	1.7	w		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Maximum Junction-to-Ambienta	R <sub>thJA</sub>	62.5	°C/W		

Notes

a. Surface Mounted on FR4 Board,  $t \le 10$  sec.

# **Si4946EY**

# Vishay Siliconix



SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit	
Static			<u> </u>				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1		3	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
7 O-t- V-h D		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			2	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			25		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	20			Α	
Drain-Source On-State Resistance <sup>b</sup>	_	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		0.045	0.055	Ω	
Drain-Source On-State Hesistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$		0.055	0.075		
Forward Transconductanceb	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.5 A		13		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2 A, V <sub>GS</sub> = 0 V		0.9	1.2	V	
Dynamic <sup>a</sup>	·						
Total Gate Charge	Qg			19	30		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 30 \text{ V}, \ V_{GS} = 10 \text{ V}, \ I_D = 4.5 \text{ A}$		4		nC	
Gate-Drain Charge	Q <sub>gd</sub>			3			
Gate Resistance	Rg		1		3.6	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DD} = 30 \text{ V, } R_L = 30 \Omega$ $I_D \cong 1 \text{ A, } V_{GEN} = 10 \text{ V, } R_G = 6 \Omega$		13	20		
Rise Time	t <sub>r</sub>			11	20		
Turn-Off Delay Time	t <sub>d(off)</sub>			36	60	ns	
Fall Time	t <sub>f</sub>			11	20	]	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2 A, di/dt = 100 A/μs		35	60		

### Notes

- For design aid only; not subject to production testing. Pulse test; pulse width  $\leq 300 \,\mu\text{s}$ , duty cycle  $\leq 2\%$ .

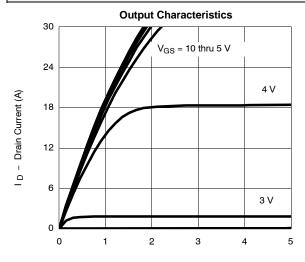
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



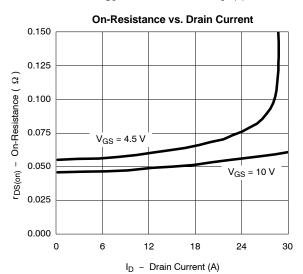




### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



V<sub>DS</sub> - Drain-to-Source Voltage (V)



V<sub>DS</sub> = 30 V I<sub>D</sub> = 4.5 A

8

8

9

9

0

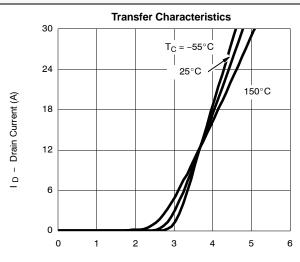
0

4

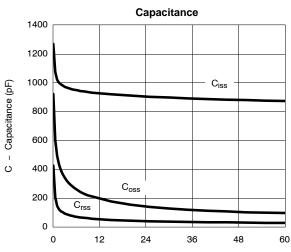
1

Q<sub>g</sub> - Total Gate Charge (nC)

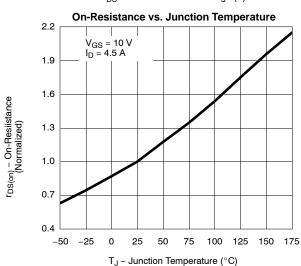
**Gate Charge** 



V<sub>GS</sub> - Gate-to-Source Voltage (V)



V<sub>DS</sub> - Drain-to-Source Voltage (V)



10

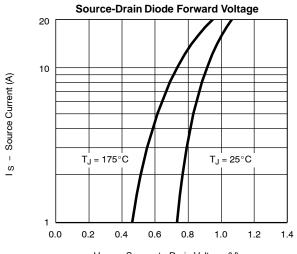
# **Vishay Siliconix**

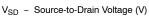


 $I_D = 4.5 A$ 

10

### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)







0.10

0.08

0.06

0.04

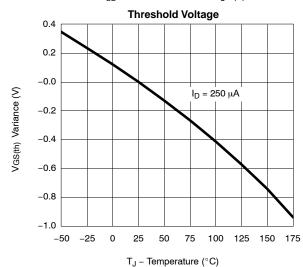
0.02

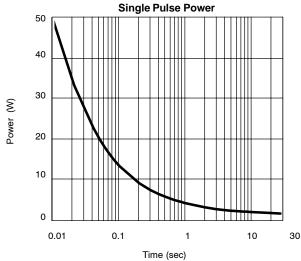
 $r_{DS(on)}$  – On-Resistance (  $\Omega$  )

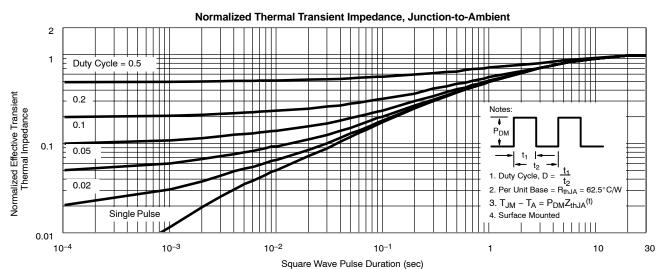




On-Resistance vs. Gate-to-Source Voltage







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